
2SC5449

Silicon NPN Triple Diffused
Character Display Horizontal Deflection Output

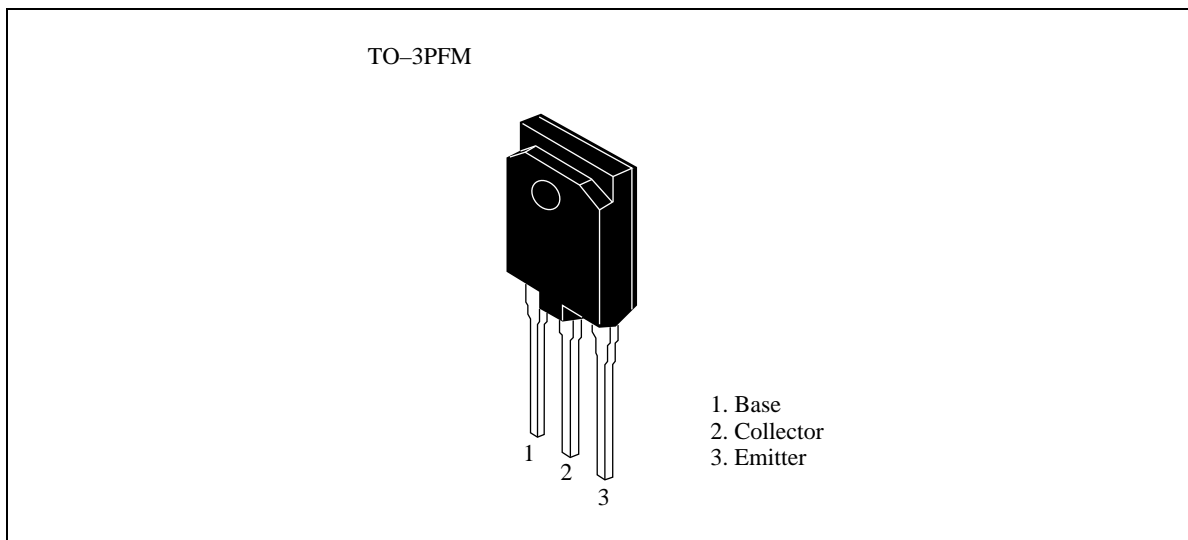
HITACHI

ADE-208-578 B (Z)
3rd. Edition
September 1997

Features

- High breakdown voltage
 $V_{CBO} = 1500 \text{ V}$
- High speed switching
 $t_r = 0.15 \text{ } \mu\text{sec}$ (typ.) at $f_H = 64 \text{ kHz}$
- Isolated package
TO-3PFM

Outline



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Absolute Maximum Ratings (Ta = 25°C)

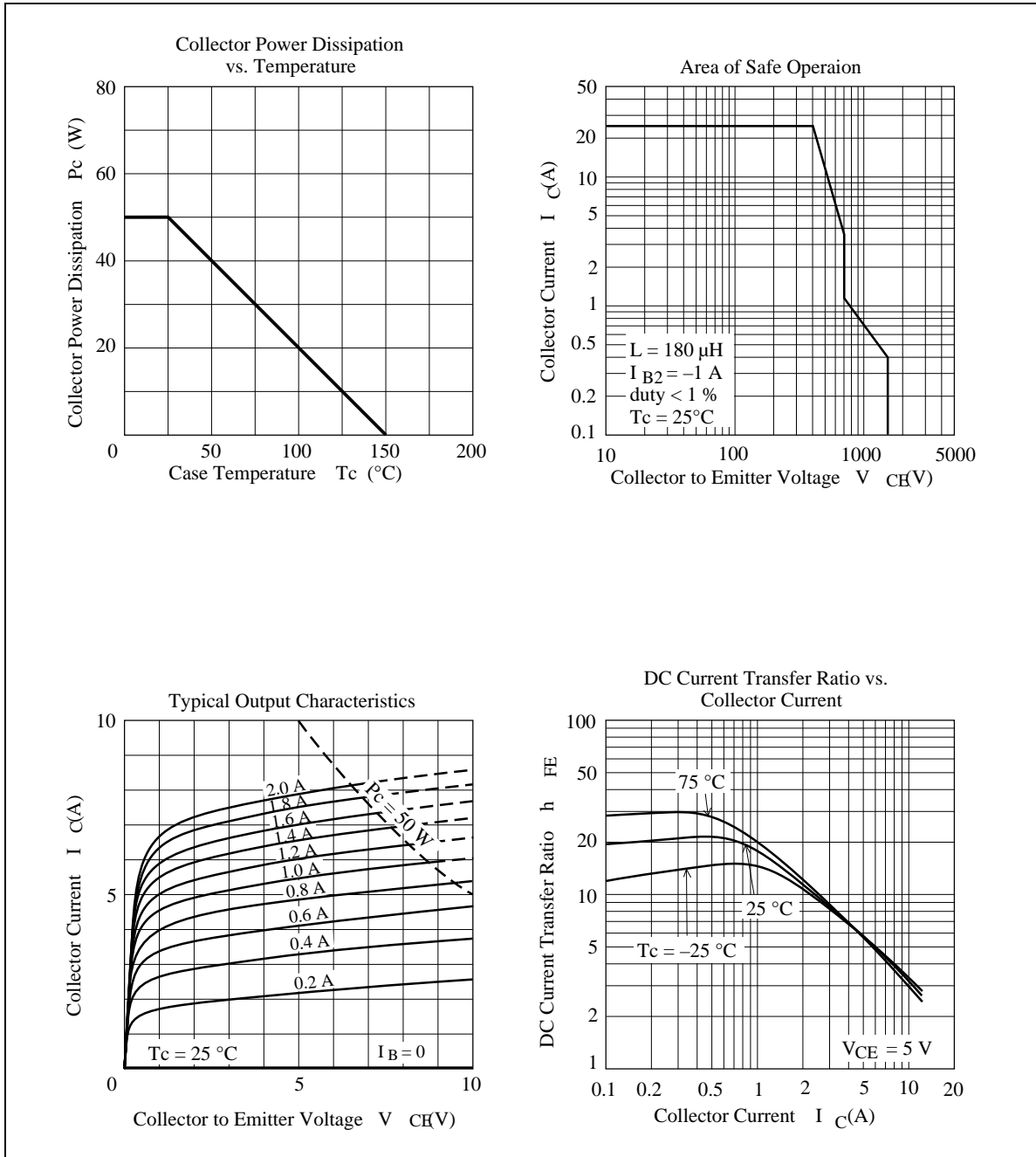
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CEO}	700	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	12	A
Collector peak current	$i_{c(peak)}$	24	A
Collector power dissipation	P_C ^{Note1}	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

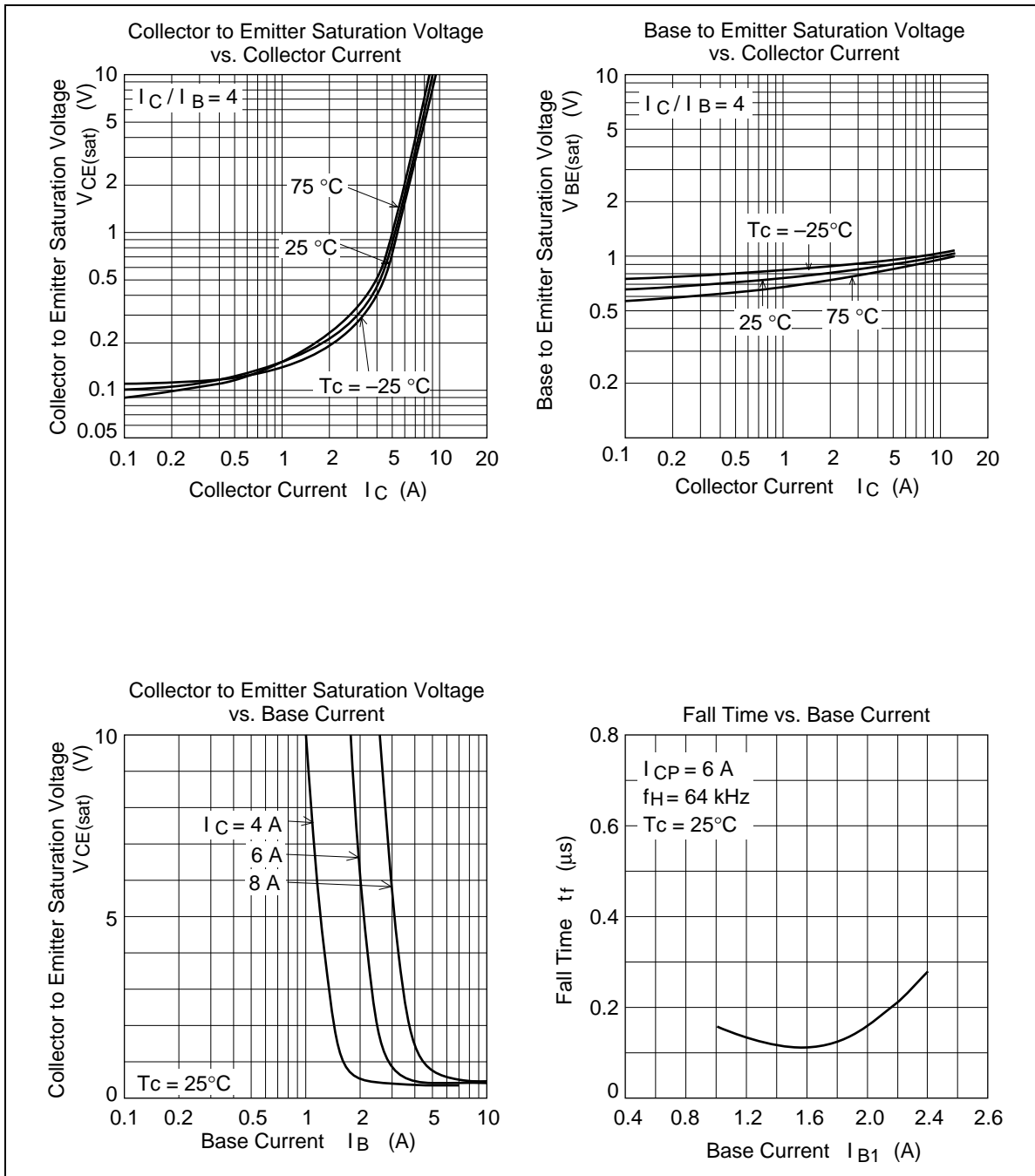
Note: 1. Value at Tc = 25°C

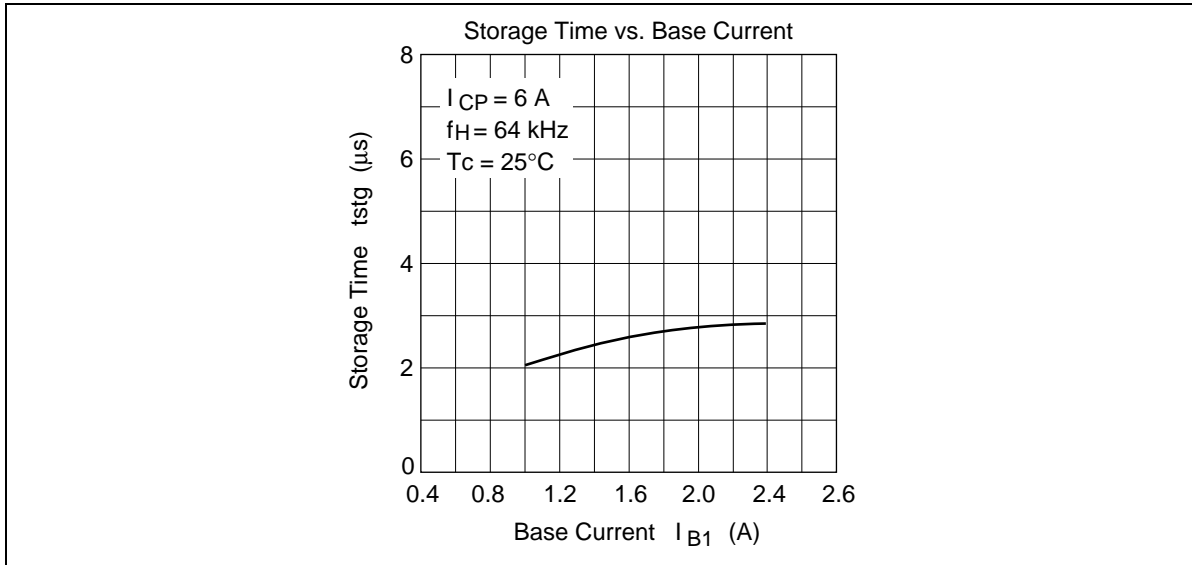
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	700	—	—	V	$I_C = 10mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10mA, I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500V, R_{BE} = 0$
DC current transfer ratio	h_{FE1}	10	—	30		$V_{CE} = 5V, I_C = 1A$
DC current transfer ratio	h_{FE2}	3.5	—	6.5		$V_{CE} = 5V, I_C = 7A$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 7A, I_B = 1.8A$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 7A, I_B = 1.8A$
Fall time	t_f	—	0.2	0.4	μs	$I_{CP} = 6A, I_{B1} = 2A$ $f_H = 31.5kHz$
Fall time	t_f	—	0.15	—	μs	$I_{CP} = 6A, I_{B1} = 1.5A$ $f_H = 64kHz$

Main Characteristics



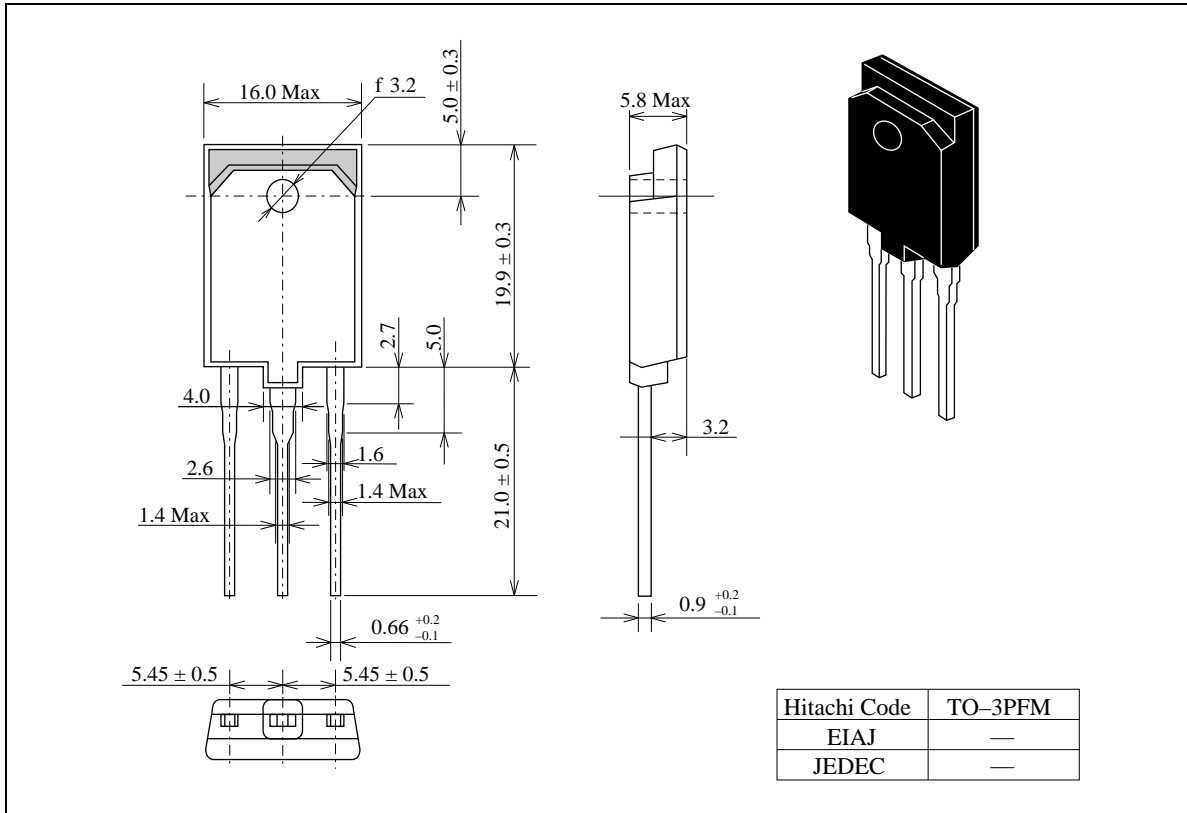




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Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

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